

Project CAIF

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Filtru Analogic:

1. Specificatii filtru:

Implementare Gm-C, Tow-Thomas 1, Banda de trecere = 0.85 MHz, aproximare Butterworth;

2. Determinarea functiei de transfer:

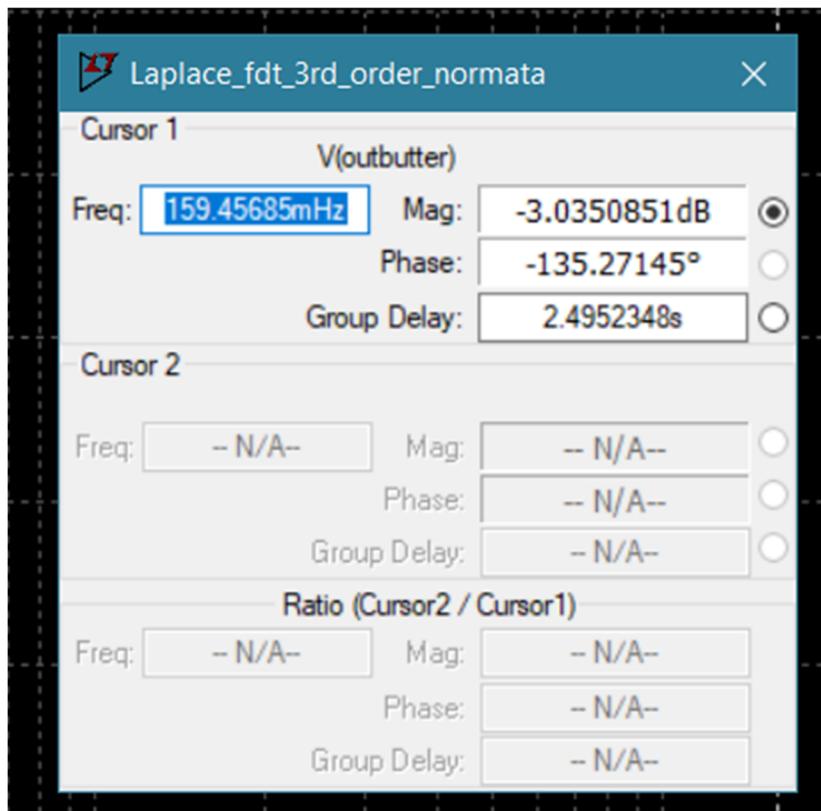
Coeficientii functiei de transfer normate de ordin 3, tip Butterworth

(banda = 1 rad/s):

$$(s+1)(s^2+s+1) \Rightarrow$$

$$c_1 = 1; c_2 = 1; d_2 = 1;$$

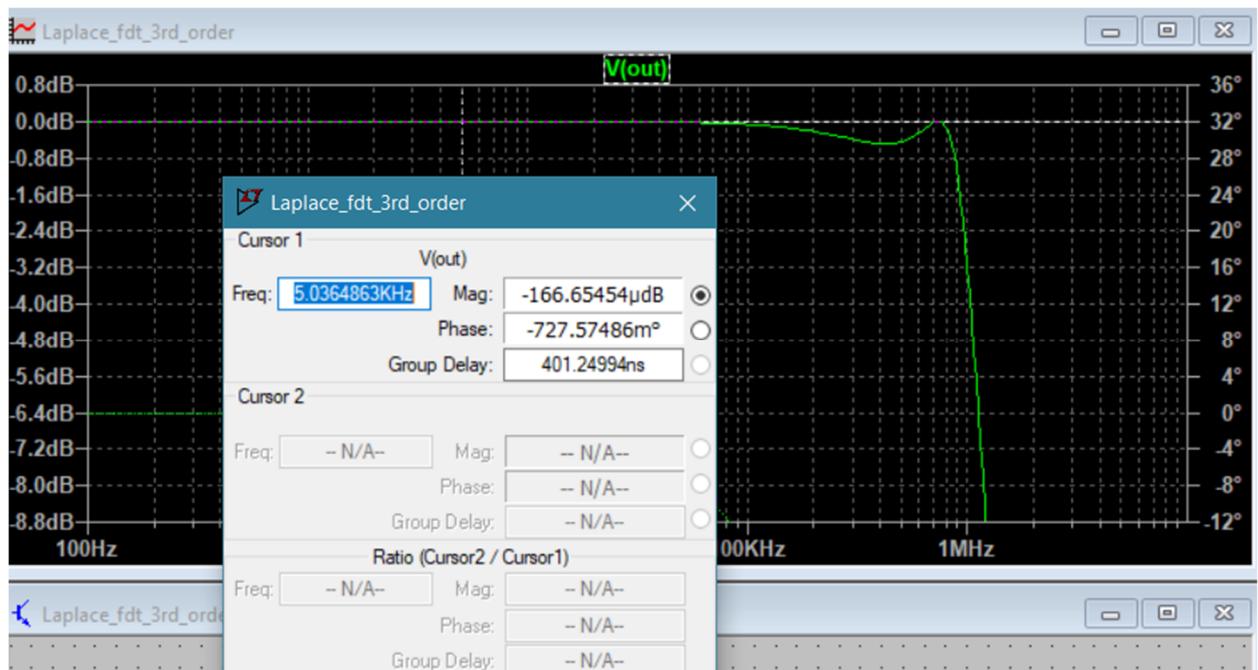
La -3 dB obtinem o banda de 159 mHz, avem nevoie de Denormare:



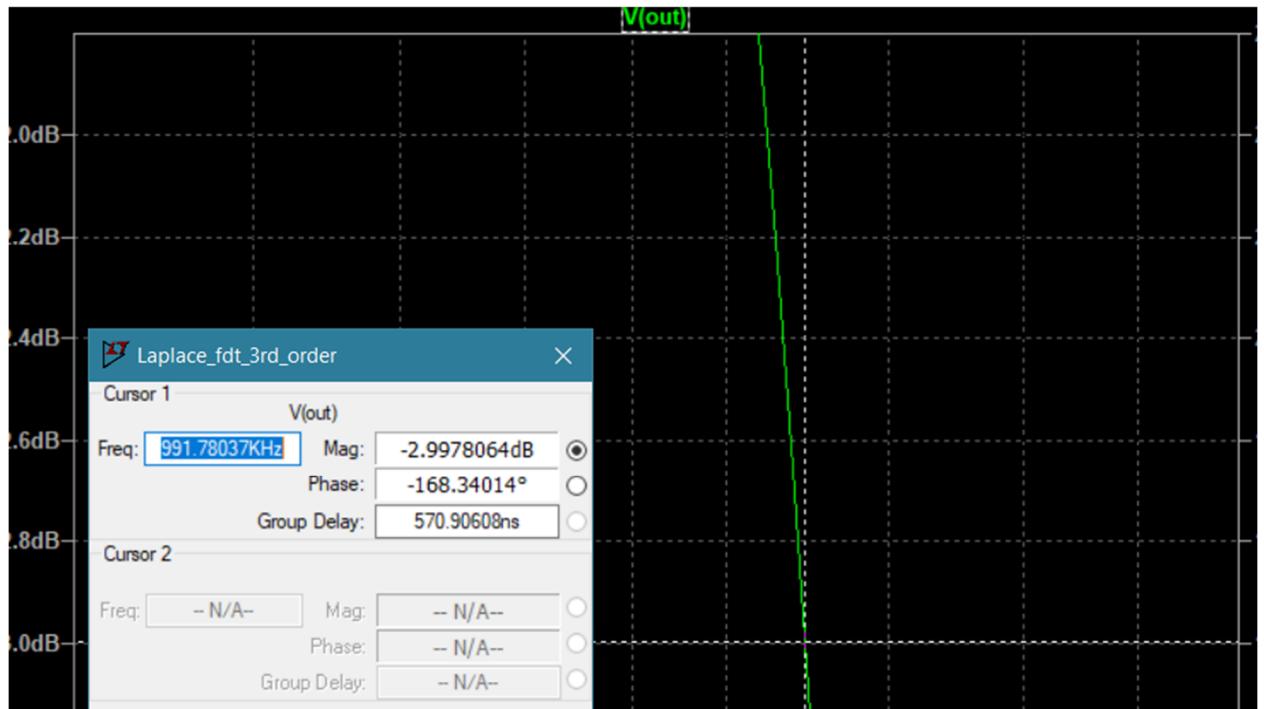
3. Denormare:

Denormalized transfer function				
$H(s) = H_0 \cdot \frac{c_{1d}}{s + c_{1d}} \cdot \frac{d_{2d}}{s^2 + c_{2d}s + d_{2d}}$				
fc=fn [Hz]	wn [Hz]	c1d	c2d	d2d
8.50E+05	5.34E+06	3.35E+06	3.35E+06	3.26E+13

Obtenim la joasa freqüència castig apropiat de 0:



Banda la -3dB este de 991kHz :



Parametrii bicuadului :

Gm1=Gm2=			
Gm3 [S]	Gm4 [S]	C2 [F]	C1 [F]
1.00E-04	1.00E-04	2.99E-11	1.03E-11

4. Dimensionarea elementelor pasive pt. integratorul Gm-C si bicuadul Tow-Thomas 1:

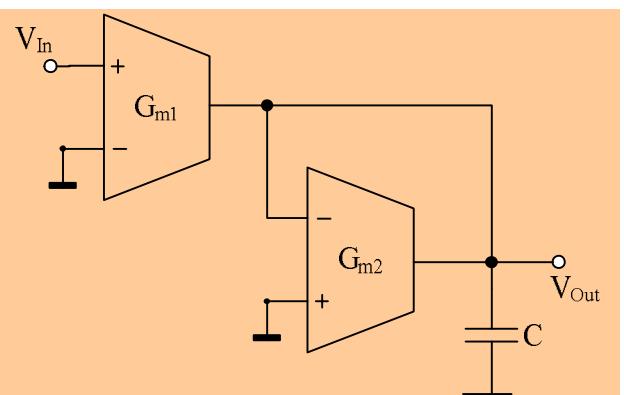
Pentru integrator Gm-C:
aleg (to be chosen) calculez (to b)

Gm1=Gm2	C
1.00E-04	2.99E-11

choose the value of $G_{m1} \Rightarrow$

Pen

$$C = \frac{G_{m1}}{\omega_{01}}; G_{m2} = \frac{G_{m1}}{H_0}.$$

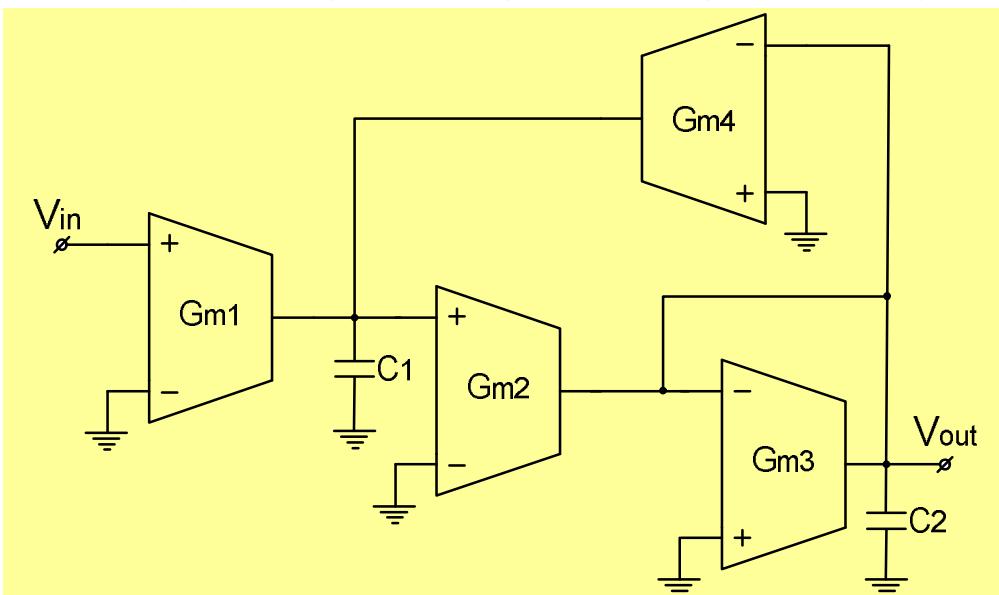


$G_{m1}=G_{m2}=$		$C_2 [F]$	$C_1 [F]$
$G_{m3} [S]$	$G_{m4} [S]$		
1.00E-04	1.00E-04	2.99E-11	1.03E-11

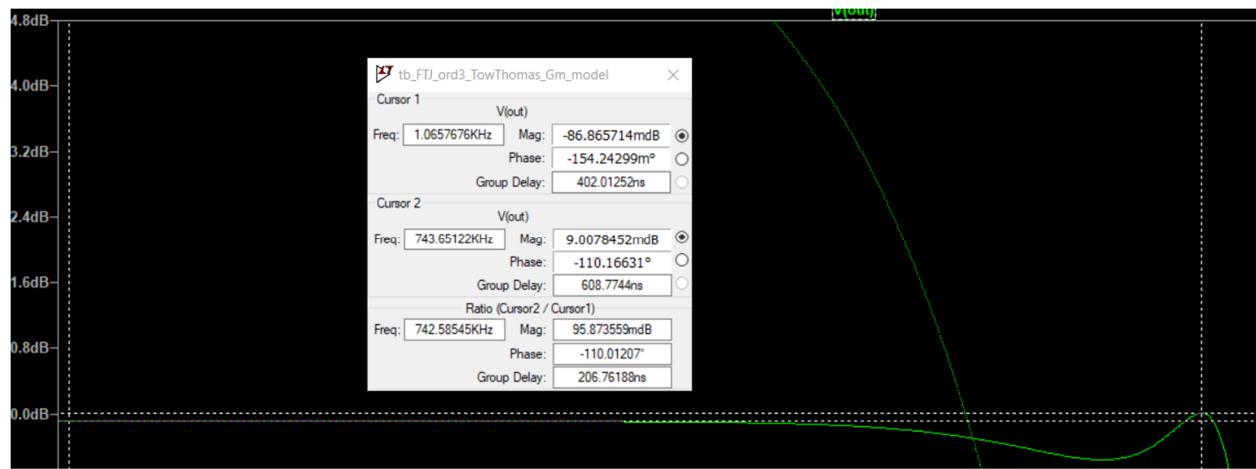
$G_{m1} = G_{m2} = G_{m3}$; choose the value of G_{m1} ;

$$C_2 = \frac{G_{m1} \cdot Q}{\omega_{02}}; C_2 = \frac{G_{m1}}{\omega_{02} \cdot Q};$$

$$G_{m4} = \frac{G_{m1}}{H_0}.$$

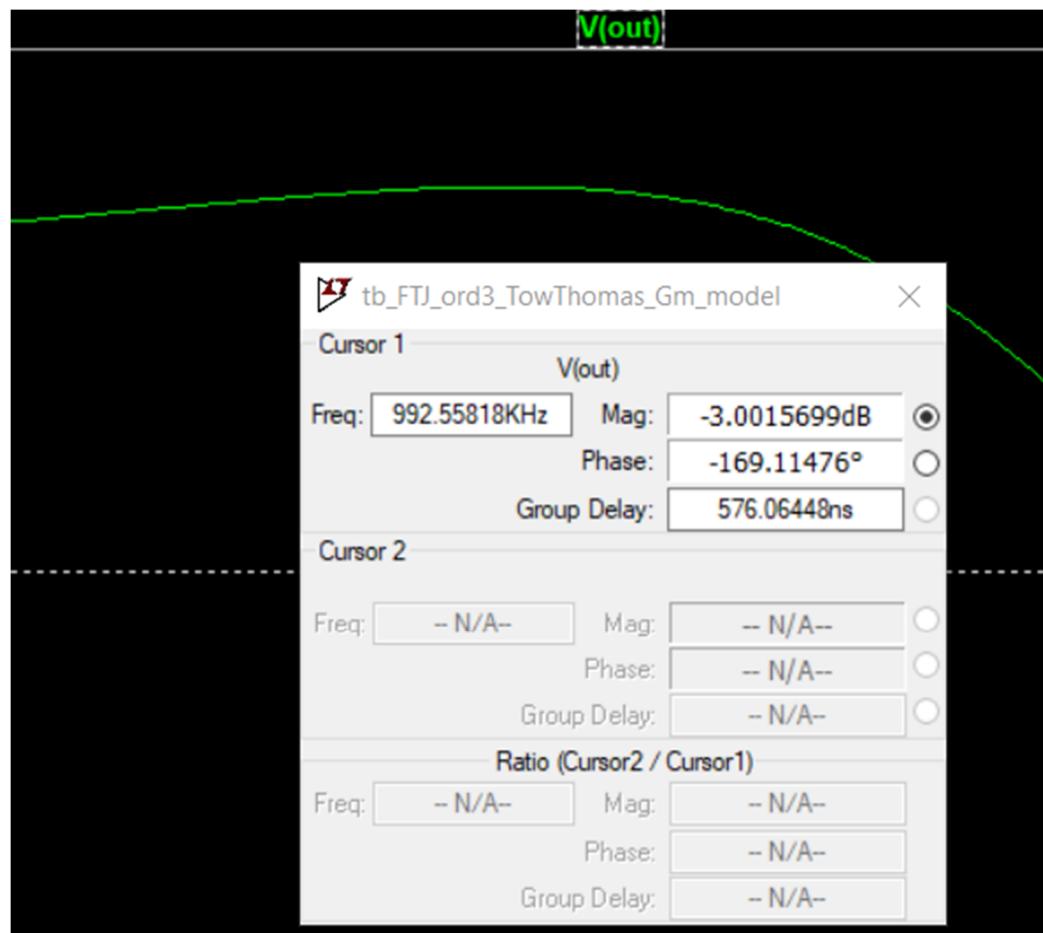


Dupa incercarea mai multor variante pentru R_{out} si F_{pol} intern, am ales sa dimensionez **Rout = 4 Meg** si **Fpol intern = 100 Meg**, astfel obtinand o eroare de **86 mdB** a castigului la joasa frecventa, si a unui gain peak de **9 mdB** :

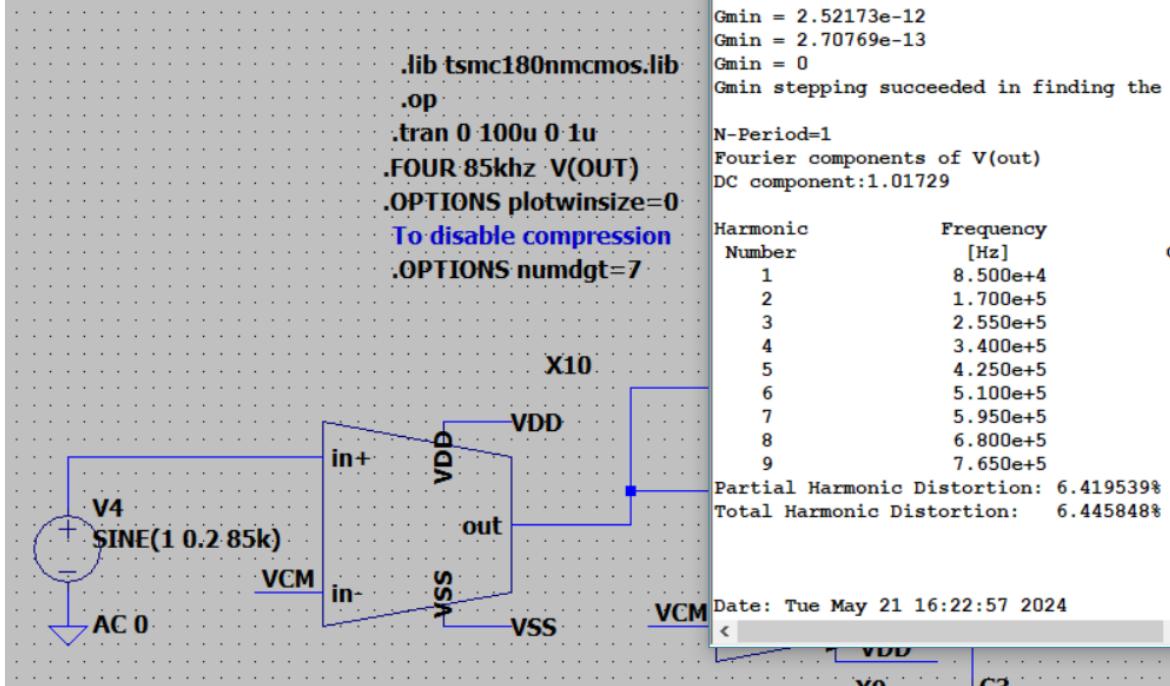


GBW = Fpol*Av(joasa frecventa) = 100 Meg;

Banda la -3dB de 992 kHz:



Nu am putut obtine un THD<1% la $F_c/10 = 85$ kHz si output amplitude 400 mV, am obtinut 6.445% (oare trebuie sa adaug in circuit condensatori de decuplare sau filtre de armonice?):

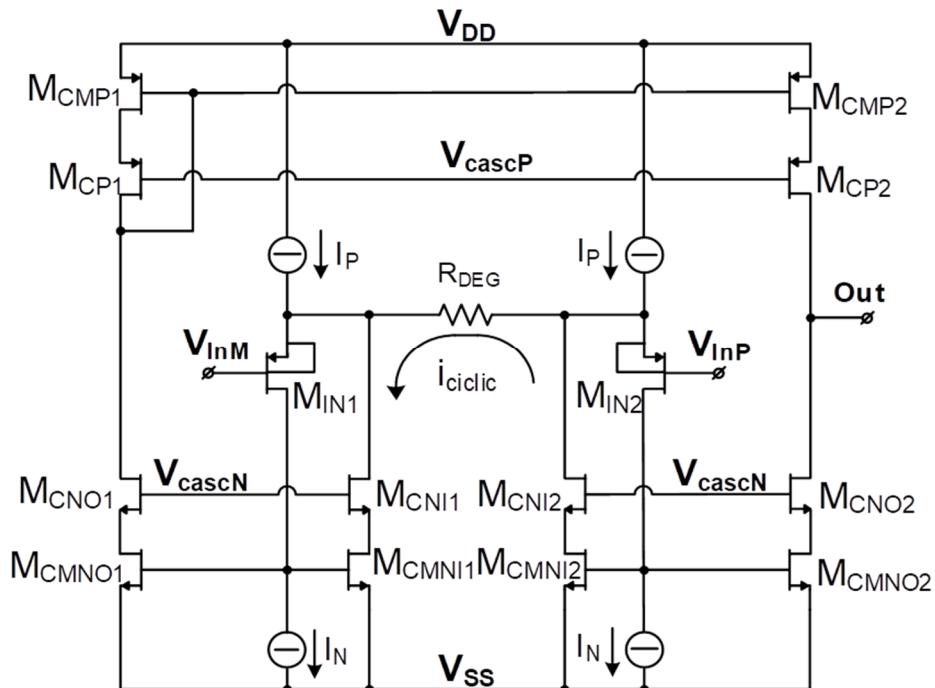


Implementare celula active pentru filtru analogic

1. Specificatii:

Tipul celulei G_m , implementare Kwan-Martin, $IDD_{max} = 2$ mA,
Tranzistori de intrare PMOS;

Aleg : $G_m = 100$ μ S;
 $R_{out} \geq 10$ MegOhmi;
 $A_{ii} = 1$;
Banda $> 10^*F_c = 8.5$ MegHz;
 $V_{dd} = 3$ V;
Tensiune de intrare 0.3 peak => 0.6 V peak-to-peak;



$$R_{deg} = 2 * A_{ii} / G_m = 20 \text{ kOhm};$$

$$I_{cyclic_max} = 0.3 / R_{deg} = 15 \mu\text{A};$$

$$I_{cmni} = (1.5 : 2) * I_{cyclic_max} = 30 \mu\text{A};$$

$$I_N = I_{cmni} / (2 : 5) = 15 \mu\text{A};$$

$$I_P = I_N + I_{cmni} = 45 \mu\text{A};$$

Bugetul de current : $2 * I_{cmni} * A_{ii} + 2 * I_P = 150 \mu\text{A} < 2 \text{ mA}$;

Pentru Vid = [-0.6 V; 0.6 V], curentul DC de la ieșire este de 76.nA:

.dc Vid -0.6 0.6 1m DC operating point: I(Vocm) = 76.633126nA

7. Se aleg Vdsat-urile pentru tranzistorii din calea de semnal: tranzistorii de intrare, din oglinzi de curent (bias); se alege o valoare intre (100mV-200mV)

$V_{DSATMIN} = 100\text{mV}$

$V_{DSAT_BIAS_NcurrentMirror} = V_{DSATCMNI} = V_{DSATCMNO} = 180\text{mV}$

$V_{DSAT_BIAS_PcurrentMirror} = V_{DSATCMP} = 180\text{mV}$

Se aleg lungimile pentru tranzistorii de intrare.

$L_{MIN} = 450\text{nm}$

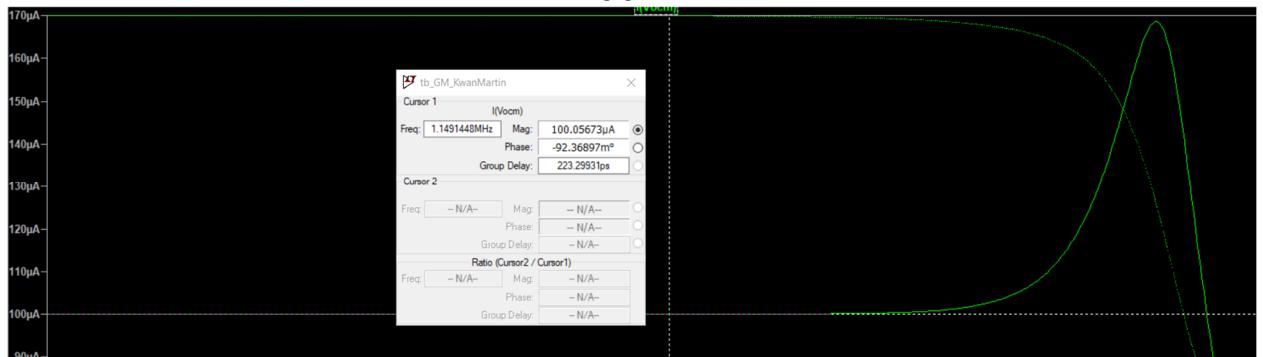
8. Se dimensioneaza tranzistorii cascoda din calea de semnal. Se alege $V_{DSAT} = 100\text{mV} - 150\text{mV}$ si $L=L_{min}$

$V_{DSAT_CascodaN} = V_{DSAT_CN} = 100\text{mV}$

$V_{DSAT_CascodaP} = V_{DSAT_CP} = 100\text{mV}$

$L_{CN} = L_{CP} = 180\text{nm}$

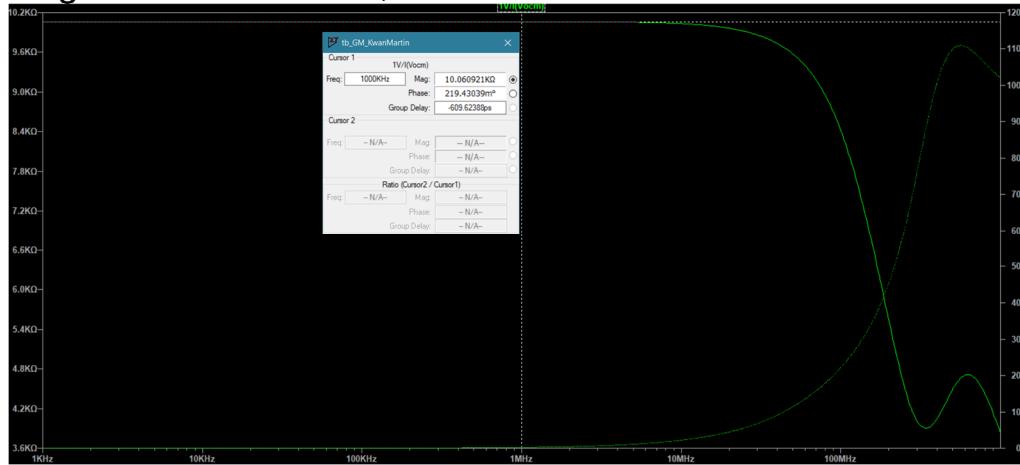
Am obtinut o transconductanta de $100\mu\text{S}$:



Analiza OP pentru tranzistori in saturatie:

Semiconductor Device Operating Points:				
--- BSIM3 MOSFETS ---				
Name:	m:x2:1	m:x2:2	m:x2:3	m:x2:4
Model:	pmos	pmos	pmos	pmos
Id:	-1.21e-04	-1.21e-04	-1.21e-04	-1.21e-04
Vgs:	-9.40e-01	-9.40e-01	-7.99e-01	-7.83e-01
Vds:	-4.54e-01	-4.71e-01	-4.86e-01	-1.53e+00
Vbs:	0.00e+00	0.00e+00	4.54e-01	4.71e-01
Vth:	-4.48e-01	-4.48e-01	-6.54e-01	-6.51e-01
Vdsat:	-3.90e-01	-3.90e-01	-1.59e-01	-1.49e-01
Gm:	4.30e-04	4.33e-04	1.41e-03	1.50e-03
Gds:	1.86e-05	1.53e-05	3.17e-05	2.79e-05
Gmb:	1.47e-04	1.48e-04	3.75e-04	3.92e-04
Cbd:	1.25e-14	1.24e-14	1.74e-14	1.48e-14
Cbs:	1.46e-14	1.46e-14	1.94e-14	1.93e-14
Cgsov:	9.60e-15	9.60e-15	1.49e-14	1.49e-14
Cgdov:	9.60e-15	9.60e-15	1.49e-14	1.49e-14
Cgbov:	7.01e-19	7.01e-19	2.61e-19	2.61e-19
dQgdVgb:	8.55e-14	8.54e-14	4.92e-14	4.91e-14
dQgdVdb:	-1.03e-14	-1.02e-14	-1.48e-14	-1.48e-14
dQgdVsb:	-7.36e-14	-7.36e-14	-3.39e-14	-3.36e-14
dQgdVgb:	-3.67e-14	-3.66e-14	-2.25e-14	-2.24e-14
dQddVdb:	2.27e-14	2.26e-14	3.22e-14	2.97e-14
dQddVsb:	3.52e-14	3.52e-14	9.65e-15	9.51e-15
dQbdVgb:	-1.22e-14	-1.22e-14	-4.19e-15	-4.20e-15
dQbdVdb:	-1.31e-14	-1.29e-14	-1.74e-14	-1.48e-14
dQbdVsb:	-2.11e-14	-2.12e-14	-1.98e-14	-1.97e-14
Name:	m:x2:6	m:x2:7	m:x2:8	m:x2:25
<				> ..

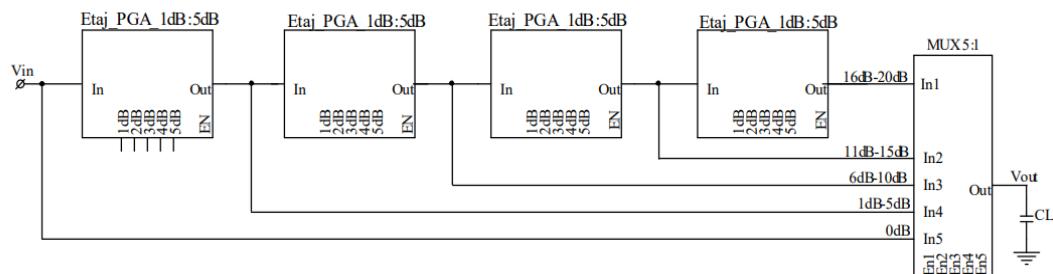
Rezistenta de iesire am obtinut de 10KiloOhmi, am modificat valorile lungimilor tranzistorilor, dar rezistenta nu se modifica.



PGA

Cerinte: Switch-uri in calea de semnal, amplificare [0 dB; 24 dB] cu pas de 2 dB, Banda de PGA > 10 MegHz, implementare cu AO;

Folosesc urmatorul model:

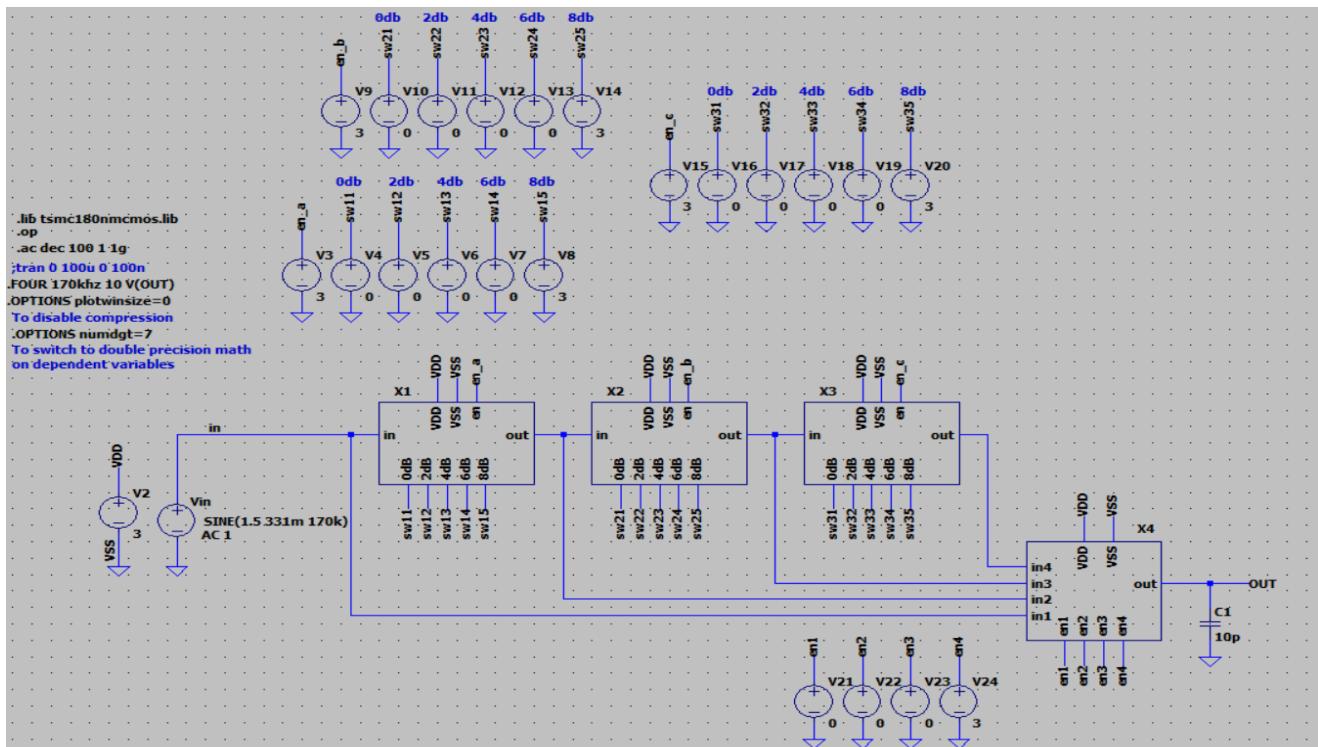


Bineintelas, in cazul meu am nevoie dor de 3 blocuri cu amplificari de (0 dB, 2 dB, 4 dB, 6 dB, 8 dB), pentru atinge amplificarea maxima 8 dB *3 = 24 dB). Aleg rezistenta de intrare de 20 kOhmi.

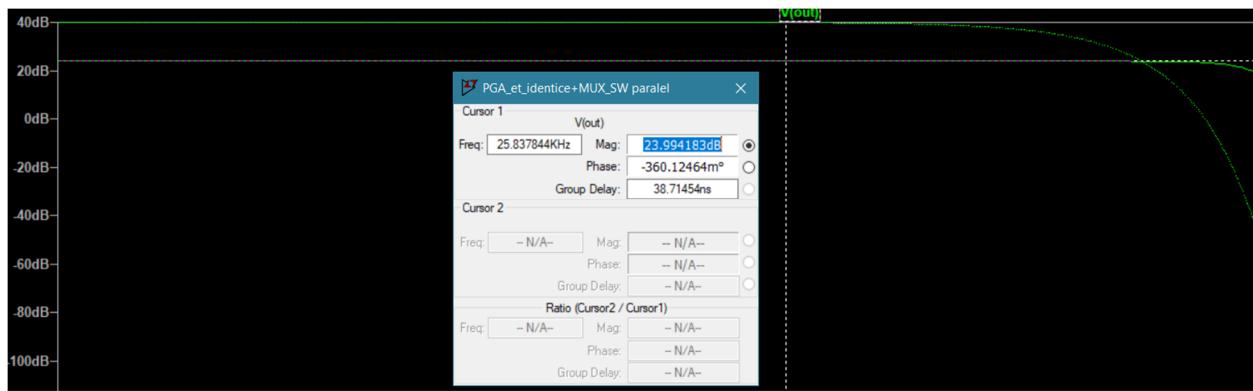
Apoi transform amplificarile din dB in linear si aflu rezistentele de reactie:

- Pentru 0 dB: $R_f = 20 \text{ k}\Omega$
- Pentru 2 dB: adăugăm $25.18 \text{ k}\Omega - 20 \text{ k}\Omega \approx 5.18 \text{ k}\Omega$
- Pentru 4 dB: adăugăm $31.70 \text{ k}\Omega - 25.18 \text{ k}\Omega \approx 6.52 \text{ k}\Omega$
- Pentru 6 dB: adăugăm $39.91 \text{ k}\Omega - 31.70 \text{ k}\Omega \approx 8.21 \text{ k}\Omega$
- Pentru 8 dB: adăugăm $50.24 \text{ k}\Omega - 39.91 \text{ k}\Omega \approx 10.33 \text{ k}\Omega$

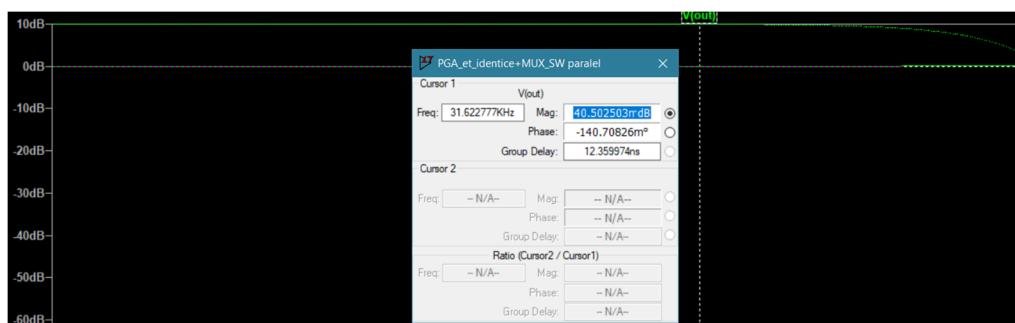
Schema electrica a circuitului:



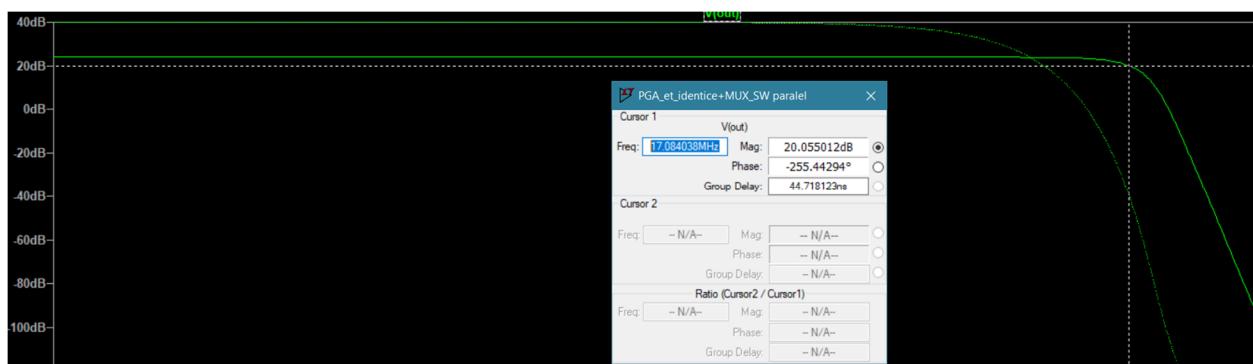
Amplificarea maxima (23.99dB):



Amplificarea minima (40 dB):



GBW(17 MHz):



Proiectare AO Cascoda-Pliata

1.Specificatii: IDD_max = 1.5 mA, implementare celula activa cascoda-plita + SC, tip tranzistori de intrare PMOS, tipul celulei active AO;

Aleg VDSsatIn = 200 mV;

Cc = 2.5pF;

Verific daca IbiasIN/Cc > 60 V/us; IbiasIN/Cc = 119 V/us;

Aleg IbiasPIN = 298 uA;

Si aleg IbiasNIN = 380 uA (considerabil mai mare);

Obtin ICM = 231 uA;

Aleg VDSsatOUT = 200 mV;

IBIASOUT/(Cc+CL) > SR;

Curentul consumat ii mai mic de 1.5 mA;

Av2 = 29.2 V/V;

VDsSatCasc = 100 mV;

Si lungimea minima a tranzistorilor cascodei 180 nm;

Mai departe dimensionez circuitul in LTSpice;

Analiza OP pentru verificarea tranzistorilor in saturatie:

--- MOSFET Transistors ---					
Name:	mbiaspin2	mbiasout	mcp2	mbiaspin1	mcp1
Model:	pmos	pmos	pmos	pmos	pmos
Id:	4.06e-05	1.89e-05	2.40e-05	4.06e-05	2.40e-05
Vgs:	-4.67e-01	-4.67e-01	-8.21e-01	-4.67e-01	-8.21e-01
Vds:	1.94e-01	1.91e-01	2.14e-03	1.94e-01	2.14e-03
Vbs:	0.00e+00	0.00e+00	-1.94e-01	0.00e+00	-1.94e-01
Vth:	-0.00e+00	-0.00e+00	-0.00e+00	-0.00e+00	-0.00e+00
Vdsat:	-6.62e-01	-6.58e-01	-8.23e-01	-6.62e-01	-8.23e-01
Gm:	7.19e-05	3.35e-05	2.92e-05	7.19e-05	2.92e-05
Gds:	1.73e-04	8.20e-05	1.12e-02	1.73e-04	1.12e-02
Gnb:	0.00e+00	0.00e+00	0.00e+00	0.00e+00	0.00e+00
Cbd:	0.00e+00	0.00e+00	0.00e+00	0.00e+00	0.00e+00
Cbs:	0.00e+00	0.00e+00	0.00e+00	0.00e+00	0.00e+00
Cgsov:	0.00e+00	0.00e+00	0.00e+00	0.00e+00	0.00e+00
Cgdov:	0.00e+00	0.00e+00	0.00e+00	0.00e+00	0.00e+00
Cgbov:	0.00e+00	0.00e+00	0.00e+00	0.00e+00	0.00e+00
Cgs:	0.00e+00	0.00e+00	0.00e+00	0.00e+00	0.00e+00
Cgd:	0.00e+00	0.00e+00	0.00e+00	0.00e+00	0.00e+00
Cgb:	0.00e+00	0.00e+00	0.00e+00	0.00e+00	0.00e+00
Name:	mbbiasp	mbcascp2	mbcascp1	mcn2	mcm2
Model:	pmos	pmos	pmos	nmos	nmos
Id:	-5.00e-05	-5.00e-05	-5.00e-05	-2.40e-05	-4.41e-06
Vgs:	-4.67e-01	-2.77e-01	-2.27e-01	1.40e+00	-5.47e-01
Vds:	-3.50e-01	-1.18e-01	-2.27e-01	-3.20e-02	-5.15e-01
Vbs:	0.00e+00	3.50e-01	4.00e-01	5.15e-01	0.00e+00
Vth:	-0.00e+00	-0.00e+00	-0.00e+00	0.00e+00	0.00e+00
Vdsat:	-4.67e-01	-2.77e-01	-2.27e-01	1.43e+00	0.00e+00

